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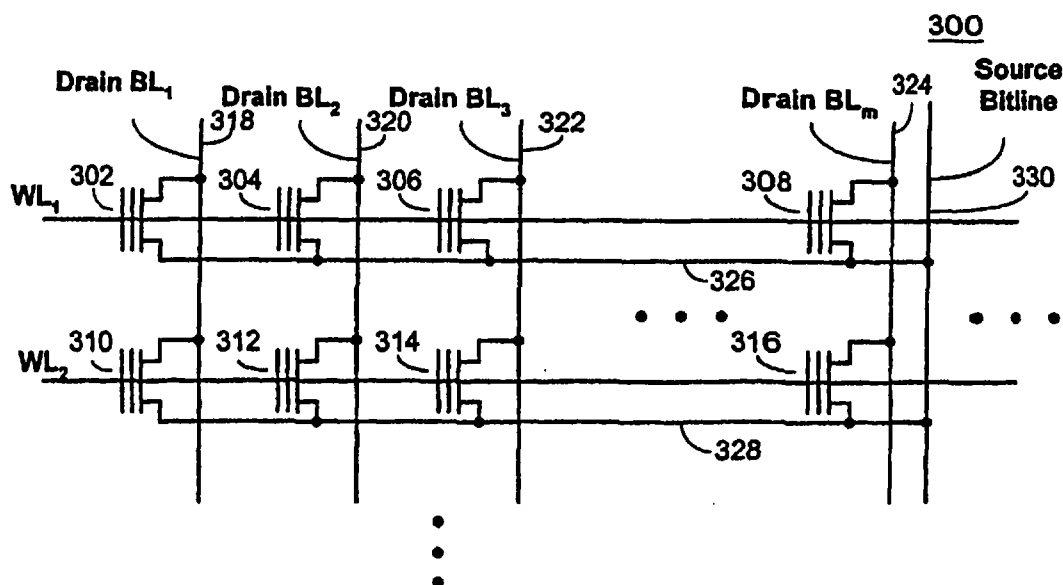


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(54) Title: 1 TRANSISTOR CELL FOR EEPROM APPLICATION



(57) Abstract: Memory devices having 1-transistor flash memory cells that in one embodiment allows bit-by-bit erase and in other embodiments allows erase of a multi-bit word. The word can be 8 bits, 16 bits, 32 bits, 64 bits or any size word. The memory devices have source bitlines that are connected to the bitline driver that controls the bitlines. The bitline driver and a wordline driver controls the voltages applied to selected bitlines, source bitlines while the wordline driver controls the voltage applied to selected wordlines to allow selected memory cells to be programmed, erased, or read.

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